

TEMPERATURE RELATIONS OF VOLT-AMPERE CHARACTERISTICS OF LIGHT EMITTING PATTERNS GaP

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It designed the improved methodology of volt-ampere characteristics (VACH) measurement with the opportunity of the settings of measurings discrete discretization step of both on the electrical voltage and on the current. It is revealed that the shape VACH GaP structures essentially depends on the mode of measurings. S-shaped character VACH and thin structure of oscillation in the field of the high currents, detected at low temperatures in a mode of discrete sampling on the current, can be explained by devastation and the subsequent occupancy of deep level which corresponds to traps of minority carriers of the current. On the low-temperature VACH the red light-emitting diodes GaP, irradiated by reactor neutrons, measured in a mode of discrete sampling on an electrical voltage, is revealed a N-shaped section where existence can be caused by the presence of disordering fields.